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本国际公布:
— 包括国际检索报告(条约第21条(3))。

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(54) Title: MEMORY AND ELECTRONIC DEVICE

(54) 发明名称: 存储器及电子设备

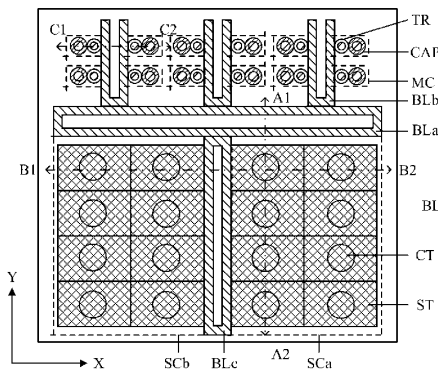


图 2A

(57) Abstract: A memory and an electronic device. The memory comprises a plurality of bit-line functional groups, a plurality of memory cells, a first step structure and a second step structure which are located on a substrate, wherein the plurality of bit-line functional groups are arranged at intervals in a first direction perpendicular to the substrate, each bit-line functional group comprises a first bit line, a second bit line coupled to the first bit line, and a third bit line coupled to the first bit line, the first bit line extends in a second direction parallel to the substrate, the second bit line and the third bit line extend in a third direction parallel to the substrate, and the second direction intersects the third direction; and the second bit line and the plurality of memory cells are located on one side of the first bit line in the third direction, the third bit line, the first step structure and the second step structure are located on the other side of the first bit line in the third direction, and the first step structure and the second step structure are located on two opposite sides of the third bit line in the second direction. The stacked structure in the memory is compact, thereby facilitating an increase in the number of cuttable dies on a wafer.

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(57) 摘要: 一种存储器及电子设备。存储器包括位于基底上的多个位线功能组、多个存储单元、第一阶梯结构和第二阶梯结构; 多个位线功能组沿垂直于基底的第一方向间隔排布, 每个位线功能组包括第一位线、与第一位线耦接的第二位线和与第一位线耦接的第三位线, 第一位线沿平行于基底的第二方向延伸, 第二位线和第三位线沿平行于基底的第三方向延伸, 第二方向与第三方向相交; 第二位线和多个存储单元位于第一位线在第三方向上的一侧, 第三位线、第一阶梯结构和第二阶梯结构位于第一位线在第三方向上的另一侧, 第一阶梯结构和第二阶梯结构位于第三位线在第二方向上的相对两侧。该存储器中的堆叠结构紧凑, 有助于提高晶圆可切割晶粒数。